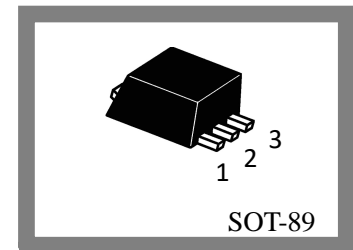


PNP Medium Power Transistor

500mW、1A、32V

MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	32	V
Collector-Base Voltage	V_{CBO}	40	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1	A
Total Device Dissipation($T_A=25^\circ\text{C}$)	P_{tot}	500	mW
Junction Temperature(Max)	T_{jM}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$



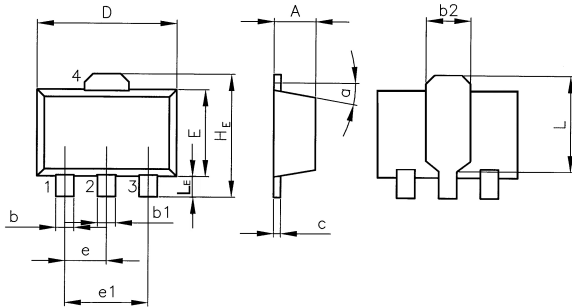
1: Base 2: Collector 3: Emitter

* Device mounted on a printed circuit board.

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

Parameter	Symbol	Test condition	Min	Typ	Max	Unit
Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	32	—	—	V
	$V_{(BR)CBO}$	$I_C=50\mu\text{A}, I_E=0$	40	—	—	V
	$V_{(BR)EBO}$	$I_E=50\mu\text{A}, I_C=0$	5	—	—	V
Collector-Cutoff Current	I_{CBO}	$V_{CB}=20\text{V}, I_E=0$	—	—	500	nA
DC Current Gain	h_{FE}	$I_C=100\text{mA}, V_{CE}=3.0\text{V}$	180	—	390	—
Collector- Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	—	—	0.50	V
Current Gain-Bandwidth Product	f_T	$I_C=50\text{mA}, V_{CE}=5\text{V}$	150	—	—	MHz

SOT-89



1 BASE 2/4 COLLECTOR 3 EMITTER

UNIT : mm

SIZE SYM.	SOT-89			SIZE SYM.	SOT-89		
	min	typ	max		min	typ	max
A		1.5		e		1.5	
b			0.65	e1		3	
b1			0.65	H _E			4.25
b2		1.6		L	2.6		2.95
c	0.25			L _E	0.8		1.2
D		4.5		a			10°
E			2.6				